

WHAT IS CLAIMED IS:

1 1. A method of forming an integrated circuit comprising:
2 providing a first diffusion region, the first diffusion region a source/drain region
3 of a first transistor;
4 providing a second diffusion region, the second diffusion region a source/drain
5 region of a second transistor;
6 providing an isolation region between the first and second diffusion regions; and
7 selectively implanting a first channel stop implant region and a second channel
8 stop implant region in the isolation region, the first channel stop implant region separate from the
9 second channel stop implant region. *wherein*

1 2. The method of claim 1 wherein the first channel stop implant region and
2 the second channel stop implant region define at least a portion of an isolation conductive path
3 between the first diffusion region and the second diffusion region.

1 3. The method of claim 2 wherein a separation distance between the first
2 channel stop implant region and the second channel stop implant region is chosen to control a
3 voltage threshold of an isolation region transistor, the isolation region transistor formed by the
4 first diffusion region, the second diffusion region, and the isolation region.

1 4. The method of claim 3 wherein when the separation distance between the
2 first channel stop implant and second channel stop implant is reduced, the threshold voltage is
3 increased. *Robert*

1 5. The method of claim 2 further comprising a third diffusion region,
2 wherein the first channel stop implant region and the second channel stop implant region form at
3 least a part of an isolation conductive path between the first diffusion region, the second
4 diffusion region, and the third diffusion region.

1 6. The method of claim 5 wherein the third diffusion region is coupled to a
2 ground pad.

1 7. The method of claim 2 further comprising providing a field oxide region
2 over the isolation region.

1 8. The method of claim 7 further comprising providing a gate over the field
2 oxide region, wherein when a threshold voltage is applied to the gate, current flows in the
3 isolation conductive path.

1 9. The method of claim 7 wherein the first diffusion region, second diffusion
2 region, and isolation region form a isolation region transistor, and the isolation region transistor
3 is used in as an electro-static discharge protection device.

1 10. The method of claim 9 wherein the first diffusion region, second diffusion
2 region, and isolation region form a isolation region transistor, and the isolation region transistor
3 is used in a charge pump circuit.

2
1 11. A method of forming an integrated circuit comprising:
2 growing a pad oxide layer on a substrate;
3 growing a silicon nitride layer on the pad oxide;
4 etching a first isolation region and a second isolation region from the silicon
5 nitride layer and the pad oxide layer;
6 depositing a spacer oxide;
7 etching the spacer oxide to form a first opening and a second opening in the first
8 isolation region, and a third opening in the second isolation region;
9 implanting a first channel stop implant region in the first opening and a second
10 channel stop implant region in the second opening in the first isolation region, and a third
11 channel stop region in the third opening in the second isolation region;
12 removing the remaining spacer oxide;
13 growing a field oxide in the first isolation region and the second isolation region;
14 removing the silicon nitride layer;
15 depositing a polysilicon layer;
16 etching the polysilicon layer; and
17 implanting a plurality of diffusion regions.

1 12. The method of claim 11 wherein the etched polysilicon layer comprises a
2 first gate region over the first isolation region and a second gate region over the second isolation
3 region.

1 13. The method of claim 12 wherein the first channel stop region and the
2 second channel stop region form at least a part of an isolation conductive path between a first
3 diffusion region and a second diffusion region, wherein the first diffusion region and the second
4 diffusion region are two of the plurality of diffusion regions.

1 14. The method of claim 13 wherein the first diffusion region and the second
2 diffusion region are at least partly defined by the first isolation region, and the plurality of
3 diffusion regions further includes a third diffusion region and a fourth diffusion region, where
4 the third diffusion region and the fourth diffusion region are at least partly defined by the second
5 isolation region, and
6 wherein current flows between the first diffusion region and the second diffusion
7 region at a first threshold voltage, and between the third diffusion region and the fourth diffusion
8 region at a second threshold voltage, the first threshold voltage less than the second threshold
9 voltage.

1 15. A method of forming an integrated circuit comprising:
2 providing a first diffusion region, the first diffusion region a source/drain region
3 of a first transistor;
4 providing a second diffusion region, the second diffusion region a source/drain
5 region of a second transistor;
6 providing a third diffusion region;
7 providing an isolation region between the first, second and third diffusion regions;
8 and
9 selectively implanting a first channel stop implant region, a second channel stop
10 implant region, and a third channel stop implant region in the isolation region, ^{wherein} the first channel
11 stop implant region, the second channel stop region, and the third channel stop region separate
12 from each other.

1 16. The method of claim 15 wherein the first channel stop implant region, the
2 second channel stop implant region, and the third channel stop implant region define at least a
3 portion of an isolation conductive path among the first diffusion region, the second diffusion
4 region, and the third diffusion region.

1 17. The method of claim 16 wherein a separation distance between the first
2 channel stop implant region and the second channel stop implant region is chosen to control a
3 voltage threshold of an isolation region transistor formed by the first diffusion region, the second
4 diffusion region, the third diffusion region, and the isolation region.

1 18. The method of claim 17 wherein the third diffusion region is coupled to a
2 ground pad.

1 19. The method of claim 17 further comprising:
2 providing a field oxide region over the isolation region.

1 20. The method of claim 19 further comprising:
2 providing a gate over the field oxide region, wherein when the threshold voltage
3 is applied to the gate, current flows among the first diffusion region, the second diffusion region,
4 and the third diffusion region.